onsemi

PNP General Purpose and NPN Bias Resistor Transistor Combination NSTB60BDW1

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- ESD Rating Human Body Model: Class 1B
 - Machine Model: Class B
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted, common for } Q_1 \text{ and } Q_2)$

Symbol	Rating	Q 1	Q ₂	Unit
V _{CEO}	Collector-Emitter Voltage	-50	50	Vdc
V _{CBO}	Collector-Base Voltage	-50	50	Vdc
V _{EBO}	Emitter-Base Voltage		5.0	Vdc
Ι _C	Collector Current – Continuous	-150	150	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

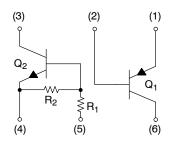
Symbol	Characteristic (One Junction Heated)	Мах	Unit
P _D	Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/°C
$R_{\theta J A}$	Thermal Resistance – Junction-to-Ambient	670 (Note 1) 490 (Note 2)	°C/W
Symbol	Characteristic (Both Junctions Heated)	Max	Unit
P _D	Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/°C
$R_{\theta JA}$	Thermal Resistance – Junction-to-Ambient	493 (Note 1) 325 (Note 2)	°C/W
$R_{\theta JL}$	Thermal Resistance – Junction-to-Lead	188 (Note 1) 208 (Note 2)	°C/W
T _J , T _{stg}	Junction and Storage Temperature	-55 to +150	°C

1. FR-4 @ Minimum Pad

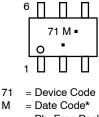
2. FR-4 @ 1.0 x 1.0 inch Pad



SOT-363 CASE 419B STYLE 1



MARKING DIAGRAM



= Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSTB60BDW1T1G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
NSVTB60BDW1T1G	SOT–363 (Pb–Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

NSTB60BDW1

Symbol	Characteristic	Min	Тур	Мах	Unit		
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _C = -50μ Adc, I _E = 0)	-50	-	-	Vdc		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage $(I_{C} = -1.0 \text{ mAdc}, I_{B} = 0)$	-50	-	-	Vdc		
V _{(BR)EBO}	Emitter–Base Breakdown Voltage (I _E = $-50 \ \mu$ Adc, I _E = 0)	-6.0	-	-	Vdc		
I _{CBO}	Collector-Base Cutoff Current ($V_{CB} = -50$ Vdc, $I_E = 0$)	-	-	-0.1	μA		
I _{EBO}	Emitter–Base Cutoff Current ($V_{EB} = -6.0 \text{ Vdc}, I_B = 0$)	-	-	-0.1	μA		
V _{CE(sat)}	Collector-Emitter Saturation Voltage ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$) (Note 3)	-	-	-0.5	Vdc		
h _{FE}	DC Current Gain (V_{CE} = -10 V, I_C = -5.0 mA) (Note 3)	120	-	560	-		
f _T	Transition Frequency ($V_{CE} = -12$ Vdc, $I_C = -2.0$ mAdc, f = 100 MHz)	-	140	_	MHz		
C _{OB}	Output Capacitance (V _{CB} = -12 Vdc, I _E = 0 Adc, f = 1.0 MHz)	-	3.5	-	pF		

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

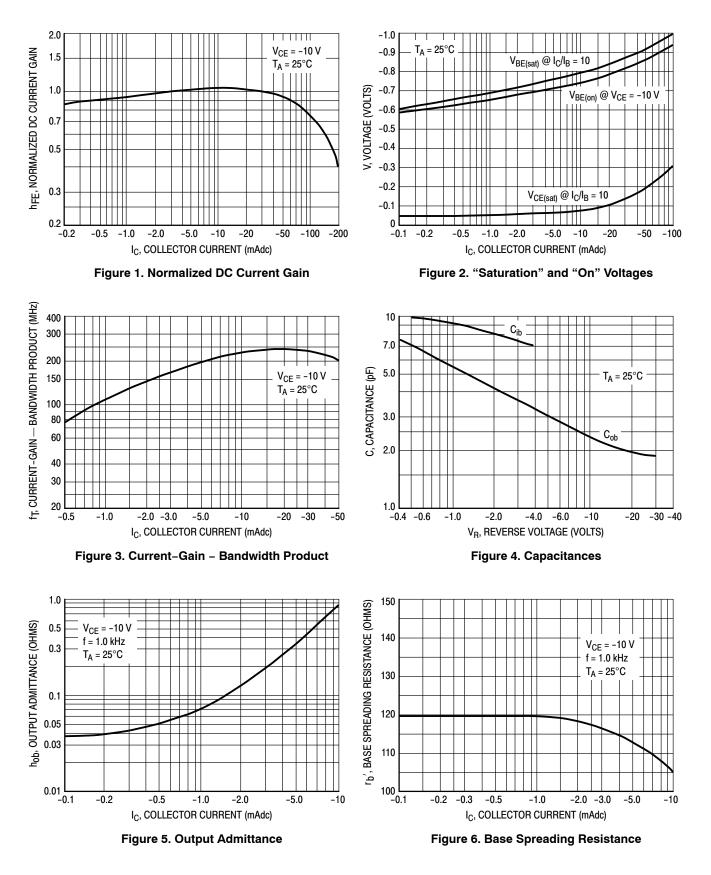
Qa

Q ₂					
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _C = 50 μ A, I _E = 0)	50	-	-	Vdc
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mA}, I_B = 0$) (Note 3)	50	-	-	Vdc
I _{CBO}	Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	-	-	100	nAdc
I _{CEO}	Collector-Emitter Cutoff Current ($V_{CE} = 50 \text{ V}, I_B = 0$)	-	-	500	nAdc
I _{EBO}	Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_{C} = 0)	-	-	0.13	mAdc
V _{CE(sat)}	Collector-Emitter Saturation Voltage $(I_{C} = 10 \text{ mA}, I_{B} = 5.0 \text{ mA})$ (Note 3)	-	-	0.25	Vdc
h _{FE}	DC Current Gain (V_{CE} = 10 V, I_{C} = 5.0 mA) (Note 3)	80	-	-	
V _{OL}	Output Voltage (on) (V_{CC} = 5.0 V, V_B = 4.0 V, R_L = 1.0 k\Omega) (Note 3)	-	-	0.2	Vdc
V _{OH}	Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 k Ω) (Note 3)	4.9	-	-	Vdc
R1	Input Resistor (Note 3)	15.4	22	28.6	kΩ
R2/R1	Resistor Ratio (Note 3)	1.70	2.13	2.55	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width < 300 µs, Duty Cycle < 2.0%

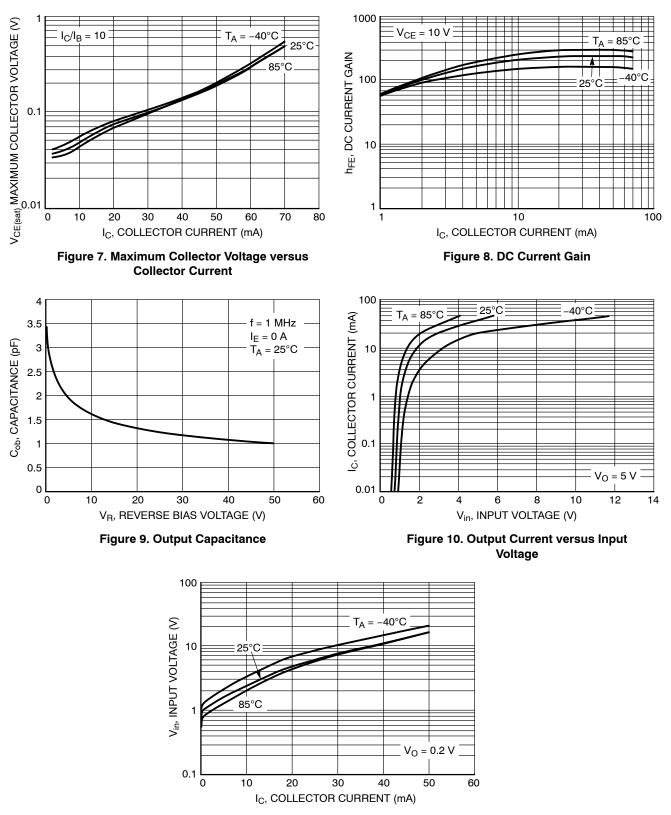
NSTB60BDW1

TYPICAL ELECTRICAL CHARACTERISTICS – PNP TRANSISTOR



NSTB60BDW1

TYPICAL ELECTRICAL CHARACTERISTICS – NPN TRANSISTOR

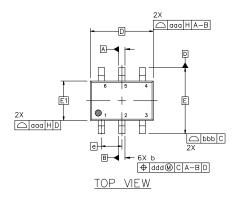




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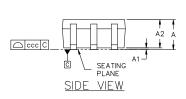
SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

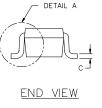
DATE 18 APR 2024

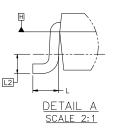




- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 3. PER END.
- 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
- DATUMS A AND B ARE DETERMINED AT DATUM H. 5.
- DIMENSIONS & AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. 7 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.







	MILLIMETERS				
DIM	MIN.	NOM.	MAX.		
А		1.10			
A1	0.00		0.10		
A2	0.70	0.90	1.00		
b	0.15	0.15 0.20 0.25			
с	0.08 0.15 0.22				
D	2.00 BSC				
E	2.10 BSC				
E1	1.25 BSC				
е		0.65 BSC)		
L	0.26 0.36 0.46				
L2	0.15 BSC				
aaa	0.15				
bbb	0.30				
ccc	0.10				
ddd	0.10				

6X 0.66 6X 0.30-2.50 0.65 PITCH

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXX = Specific Device Code Μ

GENERIC **MARKING DIAGRAM***

XXXM.

. 0

6

- = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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